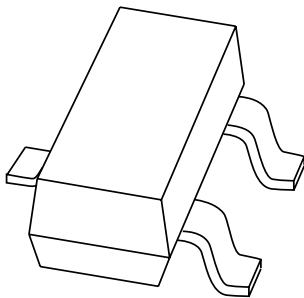


DATA SHEET



PMBT5401 PNP high-voltage transistor

Product specification
Supersedes data of 1997 Apr 09

1999 Apr 15

PNP high-voltage transistor

PMBT5401

FEATURES

- Low current (max. 300 mA)
- High voltage (max. 150 V).

APPLICATIONS

- Switching and amplification in high voltage applications such as telephony.

DESCRIPTION

PNP high-voltage transistor in a SOT23 plastic package.
NPN complement: PMBT5550.

MARKING

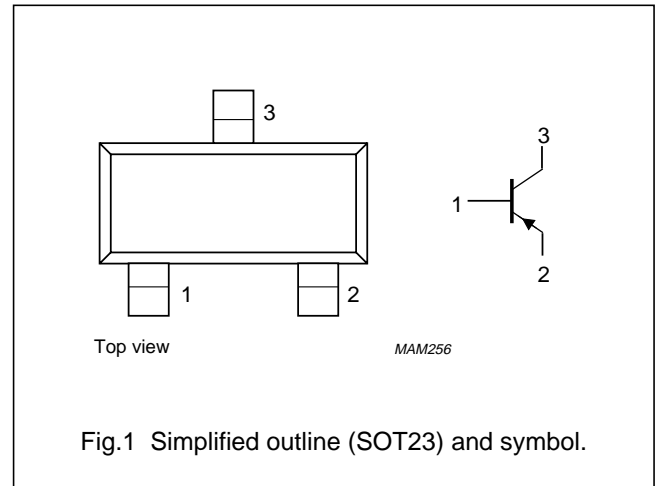
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBT5401	*2L

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	–160	V
V _{CEO}	collector-emitter voltage	open base	–	–150	V
V _{EBO}	emitter-base voltage	open collector	–	–5	V
I _C	collector current (DC)		–	–300	mA
I _{CM}	peak collector current		–	–600	mA
I _{BM}	peak base current		–	–100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	250	mW
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
T _{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP high-voltage transistor

PMBT5401

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

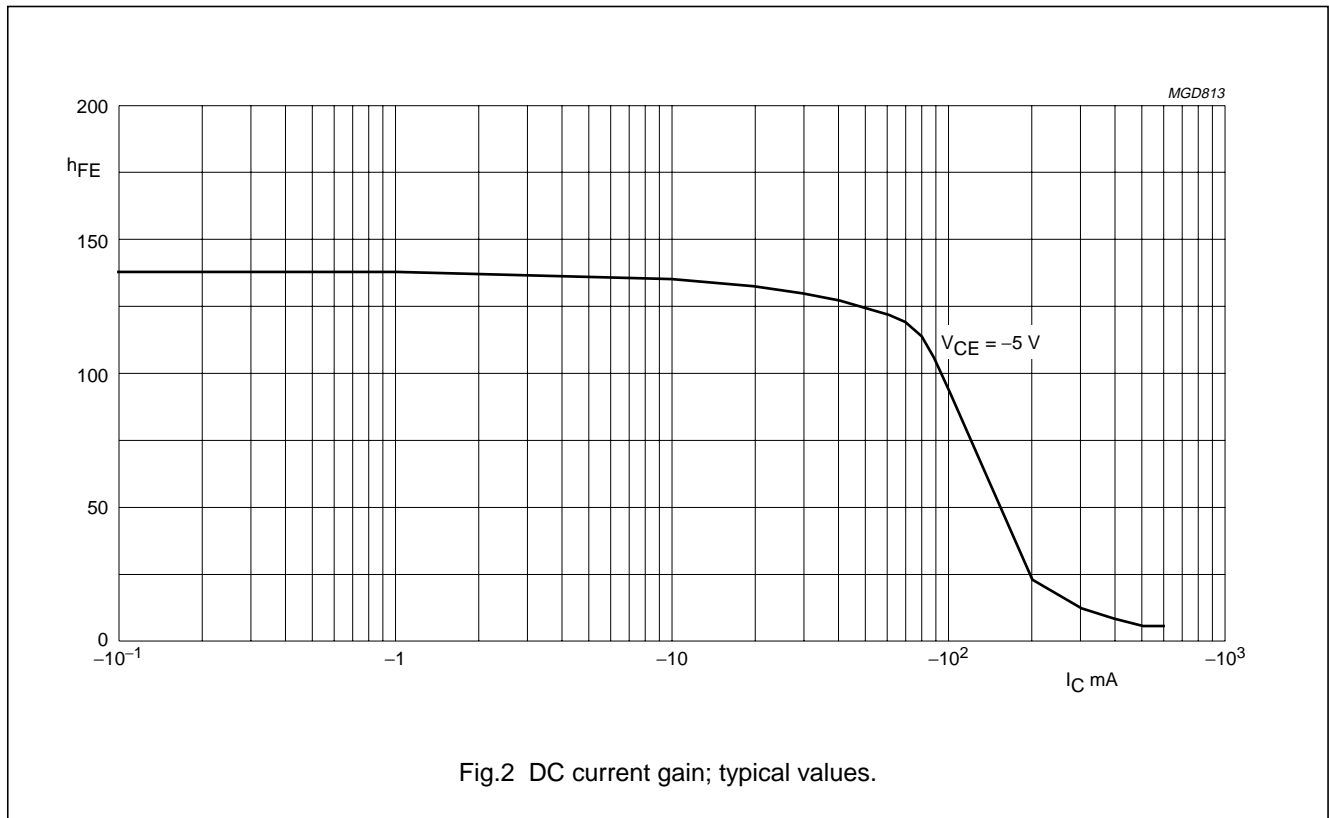
CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -120\text{ V}$	–	–50	nA
		$I_E = 0; V_{CB} = -120\text{ V}; T_{amb} = 150\text{ °C}$	–	–50	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -4\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V};$ (see Fig.2)			
		$I_C = -1\text{ mA}$	50	–	
		$I_C = -10\text{ mA}$	60	240	
		$I_C = -50\text{ mA}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–200	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	–500	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–1	V
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}$	–	–1	V
C_c	collector capacitance	$I_E = I_E = 0; V_{CB} = -10\text{ V}; f = 1\text{ MHz}$	–	6	pF
f_T	transition frequency	$I_C = -10\text{ mA}; V_{CE} = -10\text{ V};$ $f = 100\text{ MHz}; T_{amb} = 25\text{ °C}$	100	300	MHz
F	noise figure	$I_C = -200\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}; T_{amb} = 25\text{ °C}$	–	8	dB

PNP high-voltage transistor

PMBT5401



PNP high-voltage transistor

PMBT5401

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28

PNP high-voltage transistor

PMBT5401

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

PNP high-voltage transistor

PMBT5401

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